

## General Description

The GreenMOS<sup>®</sup> high voltage MOSFET utilizes charge balance technology to achieve outstanding low on-resistance and lower gate charge. It is engineered to minimize conduction loss, provide superior switching performance and robust avalanche capability.

The GreenMOS<sup>®</sup> SuperSi series is based on Oriental Semiconductor's unique device design to achieve extremely fast switching characteristics. It is the perfect replacement for the Gallium Nitride (GaN) device in high frequency operations with better ruggedness and cost. It is targeted to meet the most aggressive efficiency standards of power supply systems by pushing both performance and power density to extreme limits.

## Features

- Low  $R_{DS(ON)}$  & FOM
- Extremely low switching loss
- Excellent stability and uniformity
- Easy to design in




## Applications

- PD charger
- Large screen display
- Telecom power
- Server power

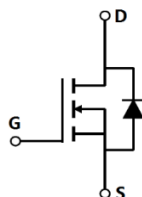
## Key Performance Parameters

Parameter	Value	Unit
$V_{DS, min} @ T_{j(max)}$	700	V
$I_D, pulse$	75	A
$R_{DS(ON), max} @ V_{GS}=10V$	125	m $\Omega$
$Q_g$	24	nC

## Marking Information

Product Name	Package	Marking
OSS65R125PZF	TO220	OSS65R125PZ

## Package & Pin Information



**Absolute Maximum Ratings** at  $T_j=25^{\circ}\text{C}$  unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-source voltage	$V_{DS}$	650	V
Gate-source voltage	$V_{GS}$	$\pm 30$	V
Continuous drain current <sup>1)</sup> , $T_C=25^{\circ}\text{C}$	$I_D$	25	A
Continuous drain current <sup>1)</sup> , $T_C=100^{\circ}\text{C}$		15.8	
Pulsed drain current <sup>2)</sup> , $T_C=25^{\circ}\text{C}$	$I_{D, pulse}$	75	A
Continuous diode forward current <sup>1)</sup> , $T_C=25^{\circ}\text{C}$	$I_S$	25	A
Diode pulsed current <sup>2)</sup> , $T_C=25^{\circ}\text{C}$	$I_{S, pulse}$	75	A
Power dissipation <sup>3)</sup> , $T_C=25^{\circ}\text{C}$	$P_D$	219	W
Single pulsed avalanche energy <sup>5)</sup>	$E_{AS}$	490	mJ
MOSFET dv/dt ruggedness, $V_{DS}=0\dots 480\text{ V}$	dv/dt	50	V/ns
Reverse diode dv/dt, $V_{DS}=0\dots 480\text{ V}$ , $I_{SD}\leq I_D$	dv/dt	50	V/ns
Operation and storage temperature	$T_{stg}, T_j$	-55 to 150	$^{\circ}\text{C}$

**Thermal Characteristics**

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	$R_{\theta JC}$	0.57	$^{\circ}\text{C/W}$
Thermal resistance, junction-ambient <sup>4)</sup>	$R_{\theta JA}$	62	$^{\circ}\text{C/W}$

**Electrical Characteristics** at  $T_j=25^{\circ}\text{C}$  unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	$BV_{DSS}$	650			V	$V_{GS}=0\text{ V}$ , $I_D=1\text{ mA}$
		700				$V_{GS}=0\text{ V}$ , $I_D=1\text{ mA}$ , $T_j=150^{\circ}\text{C}$
Gate threshold voltage	$V_{GS(th)}$	3.0		4.5	V	$V_{DS}=V_{GS}$ , $I_D=1\text{ mA}$
Drain-source on-state resistance	$R_{DS(on)}$		0.106	0.125	$\Omega$	$V_{GS}=10\text{ V}$ , $I_D=12.5\text{ A}$
			0.253			$V_{GS}=10\text{ V}$ , $I_D=12.5\text{ A}$ , $T_j=150^{\circ}\text{C}$
Gate-source leakage current	$I_{GSS}$			100	nA	$V_{GS}=30\text{ V}$
				-100		$V_{GS}=-30\text{ V}$
Drain-source leakage current	$I_{DSS}$			1	$\mu\text{A}$	$V_{DS}=650\text{ V}$ , $V_{GS}=0\text{ V}$
Gate resistance	$R_G$		4.4		$\Omega$	$f=1\text{ MHz}$ , Open drain

### Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	$C_{iss}$		1440		pF	$V_{GS}=0\text{ V}$ , $V_{DS}=50\text{ V}$ , $f=100\text{ KHz}$
Output capacitance	$C_{oss}$		163		pF	
Reverse transfer capacitance	$C_{rss}$		7.8		pF	
Effective output capacitance, energy related	$C_{o(er)}$		98		pF	$V_{GS} = 0\text{ V}$ , $V_{DS} = 0\text{V}-400\text{ V}$
Effective output capacitance, time related	$C_{o(tr)}$		498		pF	
Turn-on delay time	$t_{d(on)}$		26.8		ns	$V_{GS}=10\text{ V}$ , $V_{DS}=400\text{ V}$ , $R_G=2\ \Omega$ , $I_D=20\text{ A}$
Rise time	$t_r$		48.2		ns	
Turn-off delay time	$t_{d(off)}$		35.8		ns	
Fall time	$t_f$		3.4		ns	

### Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	$Q_g$		24		nC	$V_{GS}=10\text{ V}$ , $V_{DS}=400\text{ V}$ , $I_D=20\text{ A}$
Gate-source charge	$Q_{gs}$		10.7		nC	
Gate-drain charge	$Q_{gd}$		6.5		nC	
Gate plateau voltage	$V_{plateau}$		7.4		V	

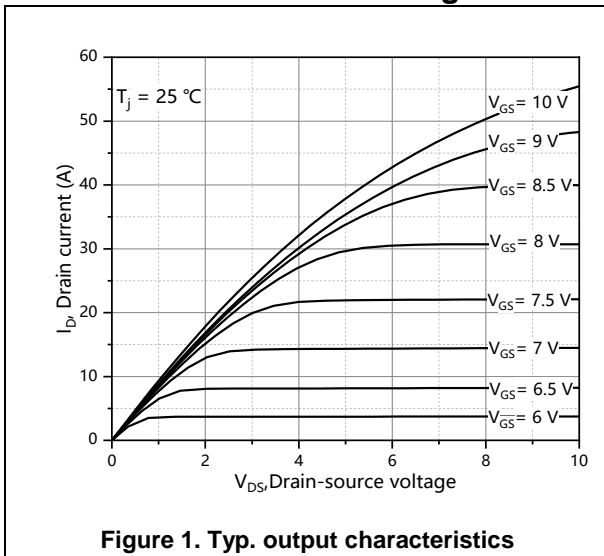
### Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward voltage	$V_{SD}$			1.3	V	$I_S=25\text{ A}$ , $V_{GS}=0\text{ V}$
Reverse recovery time	$t_{rr}$		150		ns	$V_R=400\text{ V}$ , $I_S=25\text{ A}$ , $di/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	$Q_{rr}$		0.92		$\mu\text{C}$	
Peak reverse recovery current	$I_{rrm}$		11.2		A	

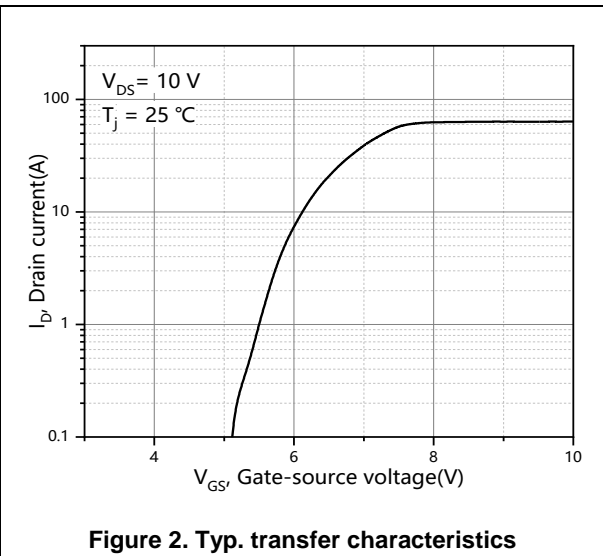
### Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3)  $P_d$  is based on max. junction temperature, using junction-case thermal resistance.
- 4) The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with  $T_a=25\text{ }^\circ\text{C}$ .
- 5)  $V_{DD}=100\text{ V}$ ,  $V_{GS}=10\text{ V}$ ,  $L=80\text{ mH}$ , starting  $T_j=25\text{ }^\circ\text{C}$ .

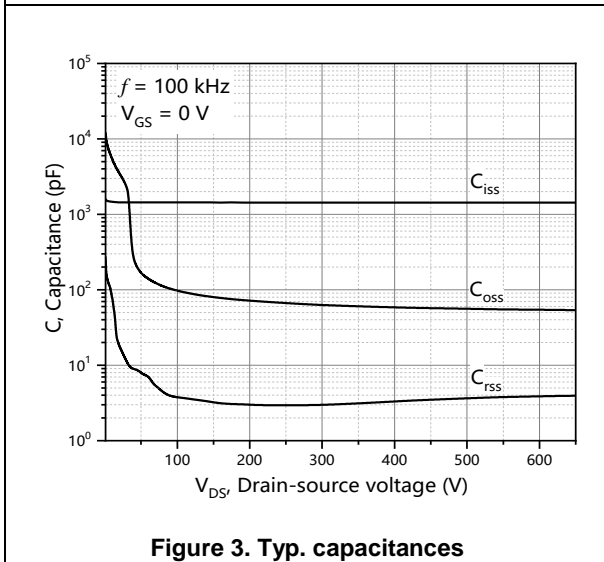
**Electrical Characteristics Diagrams**



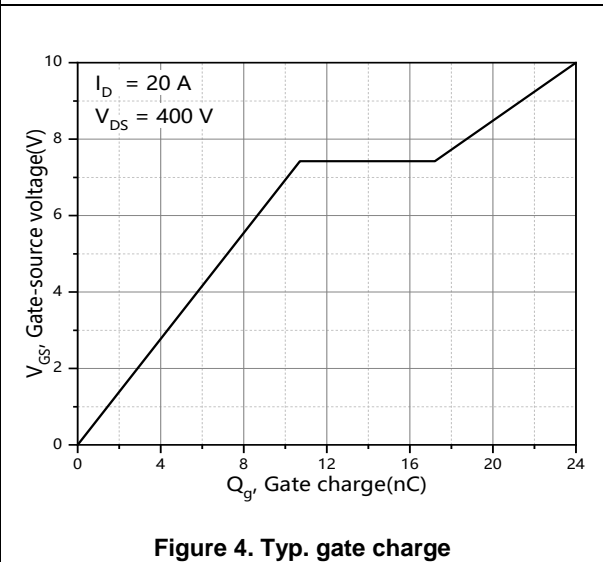
**Figure 1. Typ. output characteristics**



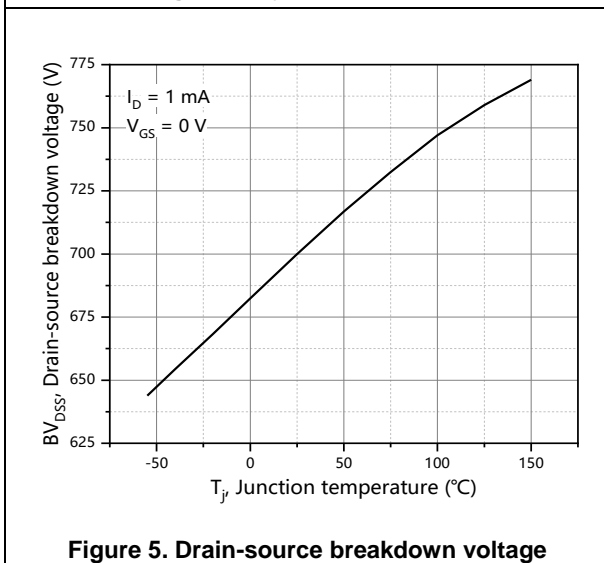
**Figure 2. Typ. transfer characteristics**



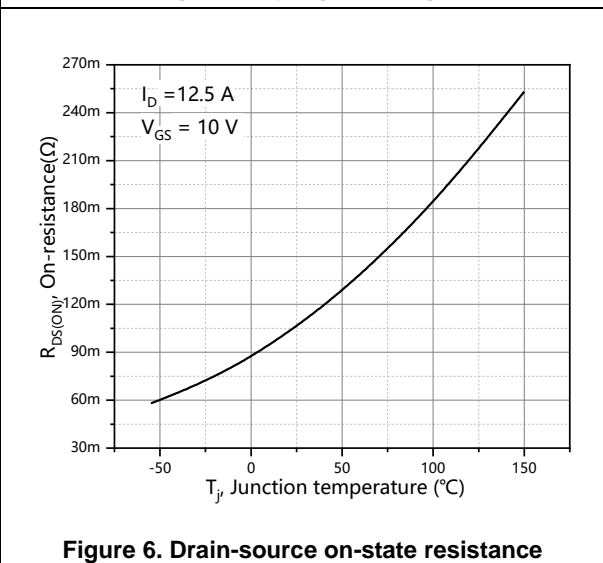
**Figure 3. Typ. capacitances**



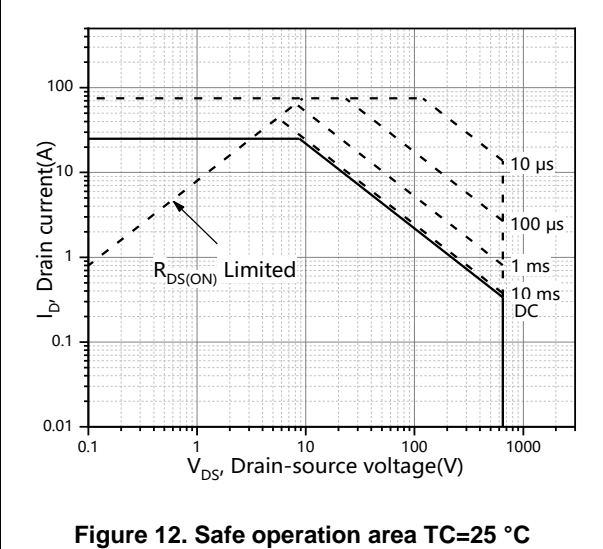
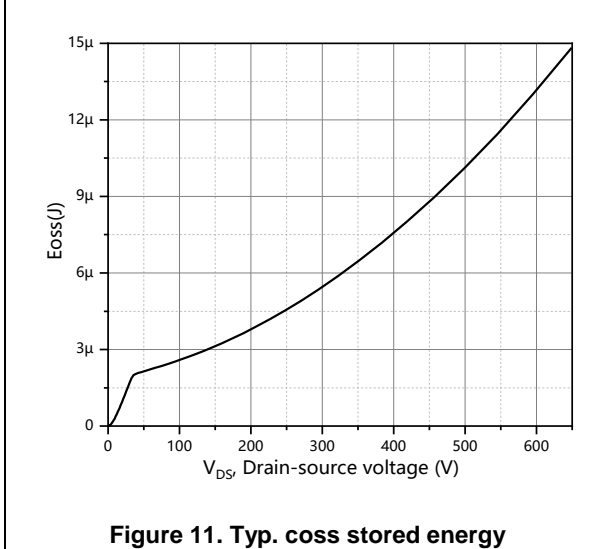
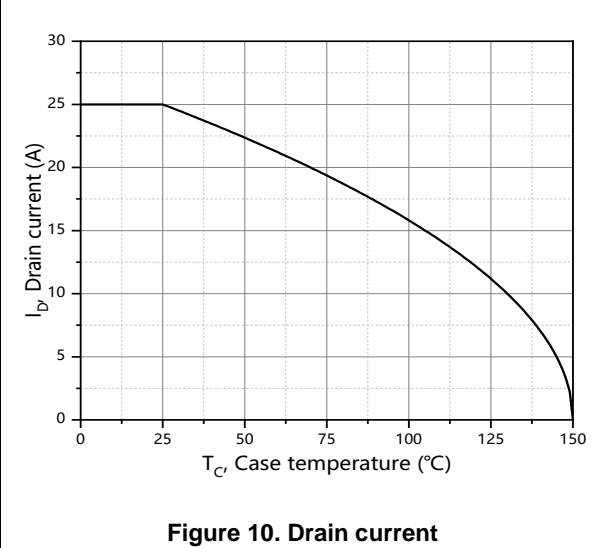
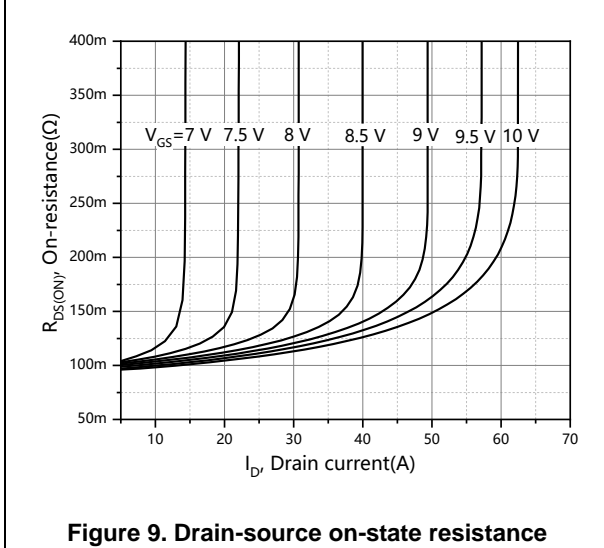
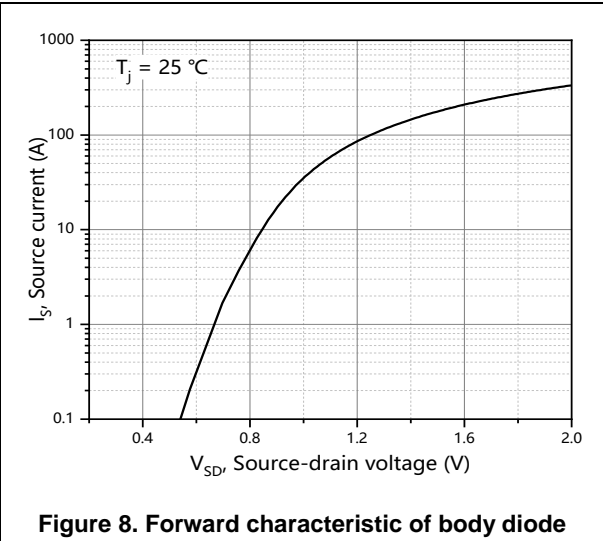
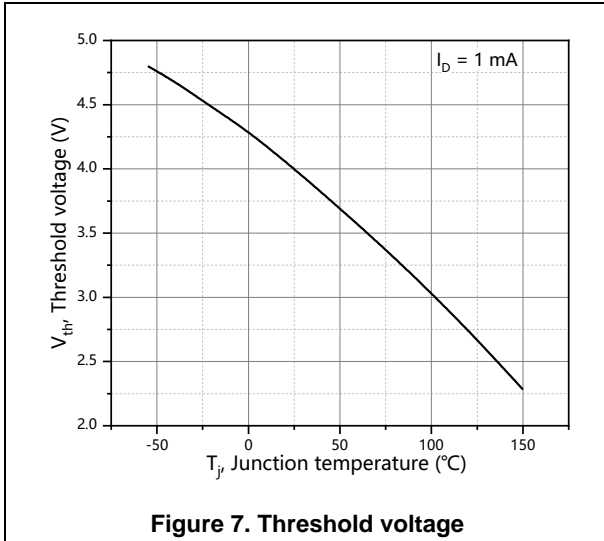
**Figure 4. Typ. gate charge**

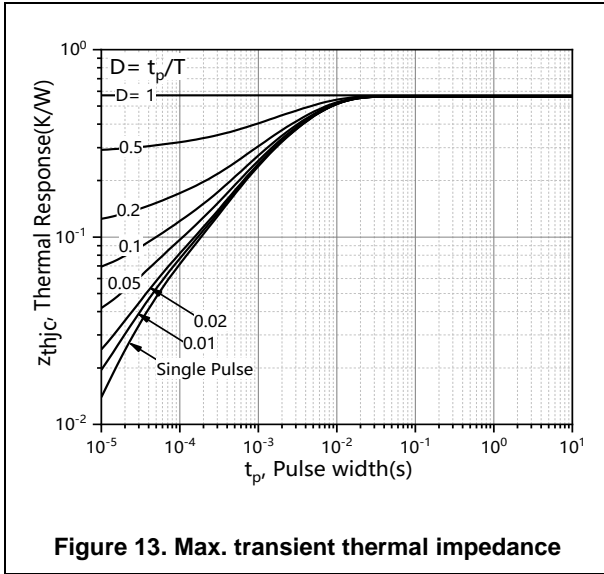


**Figure 5. Drain-source breakdown voltage**

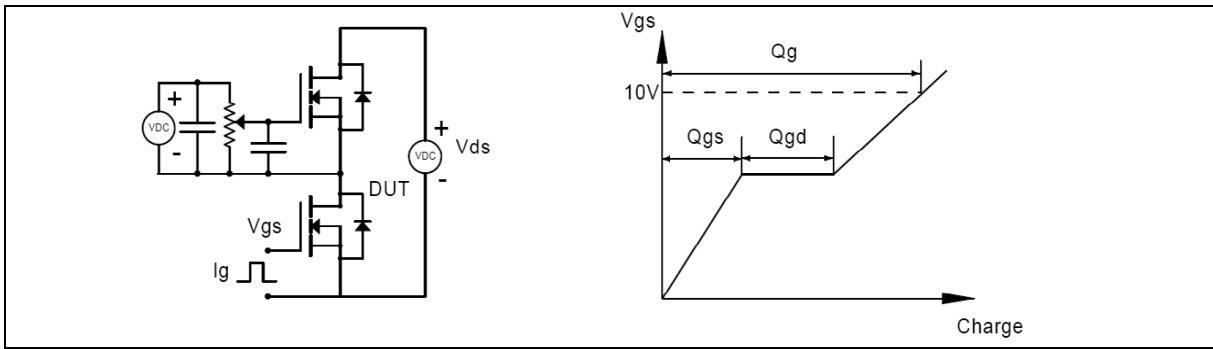


**Figure 6. Drain-source on-state resistance**

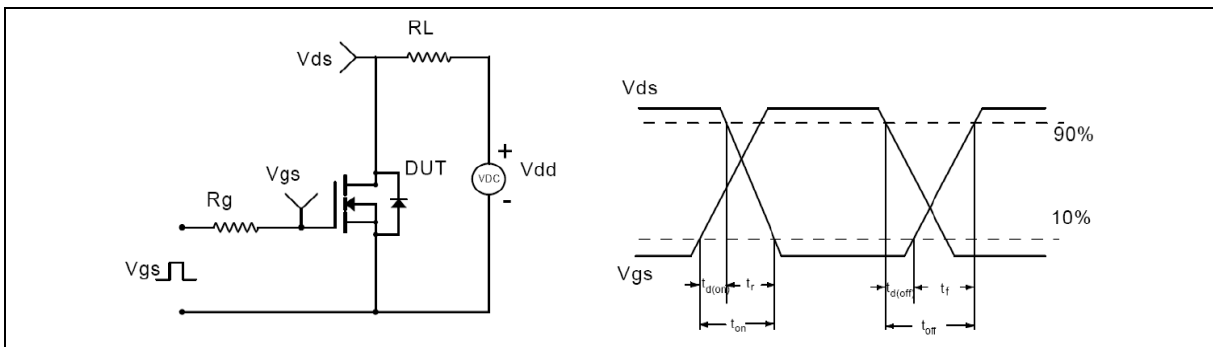




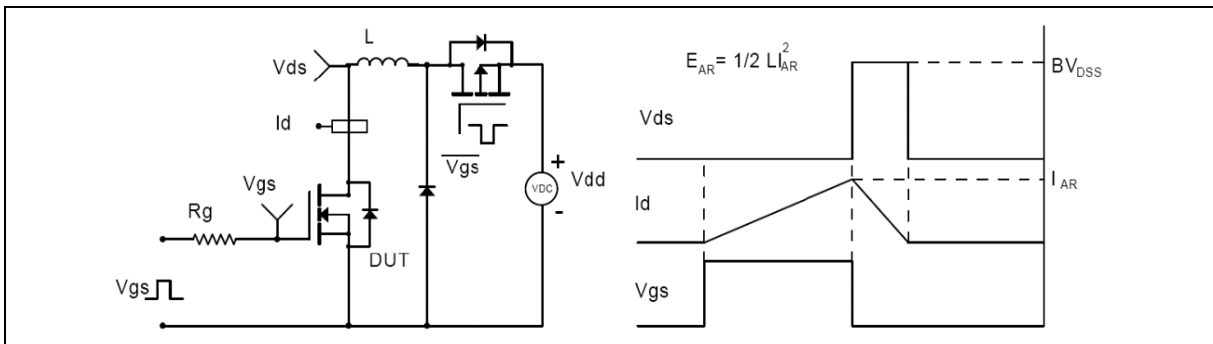
**Test circuits and waveforms**



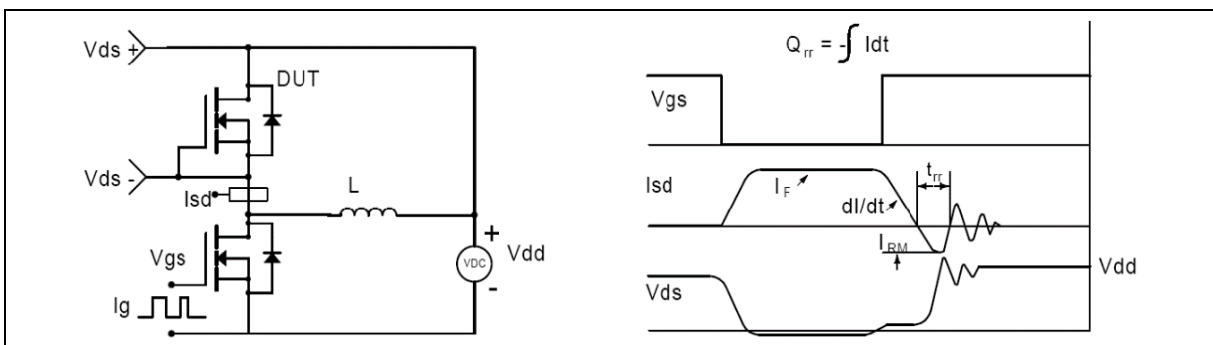
**Figure 1. Gate charge test circuit & waveform**



**Figure 2. Switching time test circuit & waveforms**

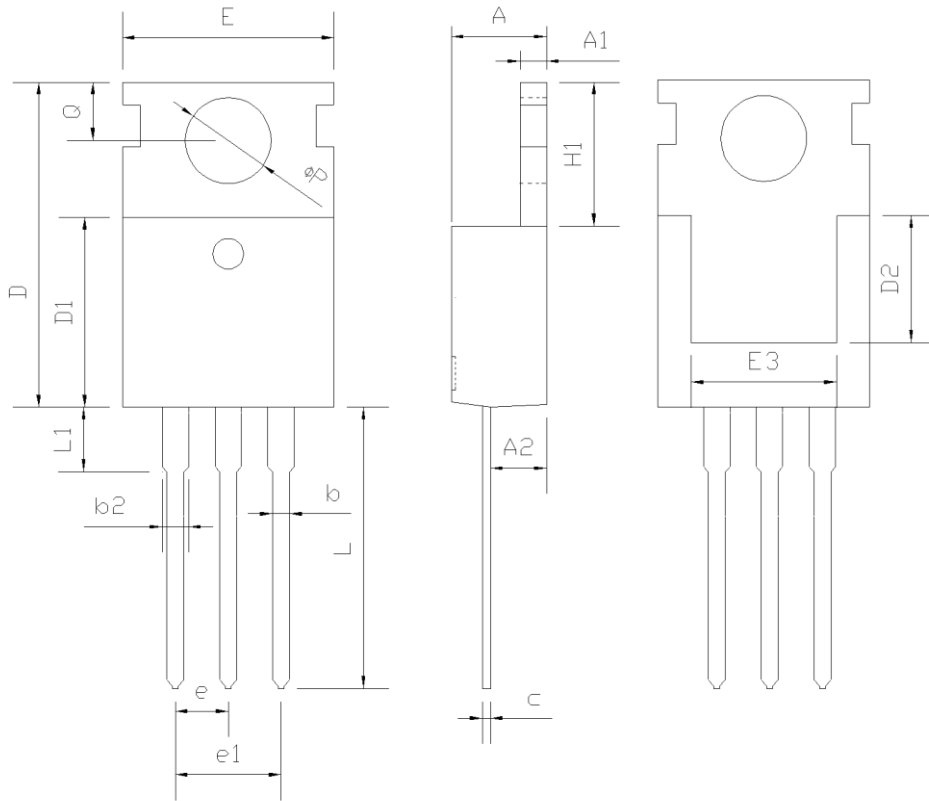


**Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms**



**Figure 4. Diode reverse recovery test circuit & waveforms**

**Package Information**



Symbol	mm		
	Min	Nom	Max
A	4.37	4.57	4.77
A1	1.25	1.30	1.45
A2	2.20	2.40	2.60
b	0.70	0.80	0.95
b2	1.17	1.27	1.47
c	0.40	0.50	0.65
D	15.10	15.60	16.10
D1	8.80	9.10	9.40
D2	5.50	-	-
E	9.70	10.00	10.30
E3	7.00	-	-
e	2.54 BSC		
e1	5.08 BSC		
H1	6.25	6.50	6.85
L	12.75	13.50	13.80
L1	-	3.10	3.40
ΦP	3.40	3.60	3.80
Q	2.60	2.80	3.00

Version 1: TO220-P package outline dimension



## Ordering Information

Package Type	Units/ Tube	Tubes/ Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
TO220-P	50	20	1000	6	6000

## Product Information

Product	Package	Pb Free	RoHS	Halogen Free
OSS65R125PZF	TO220	yes	yes	yes

## Legal Disclaimer

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